



Mini FETs from Diodes Incorporated Use 40% Less Space

Plano, Texas – January 09, 2015 – Diodes Incorporated (Nasdaq: DIOD), a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete, logic and analog semiconductor markets, today has extended its line of ultra-small discrete products for space-critical product design. The company has announced a trio of small-signal MOSFETs in the tiny DFN0606 package: 20V and 30V rated N-channel transistors and a 30V rated p-channel part. With a footprint measuring only 0.6mm x 0.6mm, each device takes 40% less board space than the commonly used DFN1006 (aka SOT883) packaged MOSFETs, making them an ideal choice for next-generation wearable tech, tablets and smartphones.

Able to deliver better or equivalent electrical performance than many of the larger package parts, the DMN2990UFZ (20V nMOS), the DMN31D5UFZ (30V nMOS) and DMP32D9UFZ (30V pMOS) have been designed to minimize on-state resistance while still maintaining a superior switching performance. In addition, a typical threshold voltage of less than 1V means a lower 'turn-on', suiting single-cell operation.

These tiny MOSFETs are well-suited for high-efficiency power-management duties and as general-purpose interfacing and simple analog switches. Circuit power density gets a boost too, with the DFN0606 parts achieving a power dissipation of 300mW. Further information is available at www.diodes.com.

About Diodes Incorporated

Diodes Incorporated (Nasdaq: DIOD), a Standard and Poor's SmallCap 600 and Russell 3000 Index company, is a leading global manufacturer and supplier of high-quality application specific standard products within the broad discrete,

logic and analog semiconductor markets. Diodes serves the consumer electronics, computing, communications, industrial, and automotive markets. Diodes' products include diodes, rectifiers, transistors, MOSFETs, protection devices, functional specific arrays, single gate logic, amplifiers and comparators, Hall-effect and temperature sensors; power management devices, including LED drivers, AC-DC converters and controllers, DC-DC switching and linear voltage regulators, and voltage references along with special function devices, such as USB power switches, load switches, voltage supervisors, and motor controllers. Diodes' corporate headquarters, logistics center, and Americas' sales office are located in Plano, Texas. Design, marketing, and engineering centers are located in Plano; San Jose, California; Taipei, Taiwan; Manchester, England; and Neuhaus, Germany. Diodes' wafer fabrication facilities are located in Kansas City, Missouri and Manchester, with two more located in Shanghai, China. In addition, two assembly-test facilities are located in Shanghai; two are located in Chengdu, China, with one in Neuhaus and one in Taipei. Additional engineering, sales, warehouse, and logistics offices are located in Fort Worth, Texas; Taipei; Hong Kong; Manchester; Shanghai; Shenzhen, China; Seongnam-si, South Korea; Suwon, South Korea; Tokyo, Japan; and Munich, Germany, with support offices throughout the world. For further information, including SEC filings, visit Diodes' website at <http://www.diodes.com>.

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